

< IGBT MODULES >

# CM75DY-34A

HIGH POWER SWITCHING USE  
INSULATED TYPE



**Dual (Half-Bridge)**

Collector current  $I_C$  ..... **75 A**  
 Collector-emitter voltage  $V_{CES}$  ..... **1700 V**  
 Maximum junction temperature  $T_{jmax}$  ..... **150 °C**

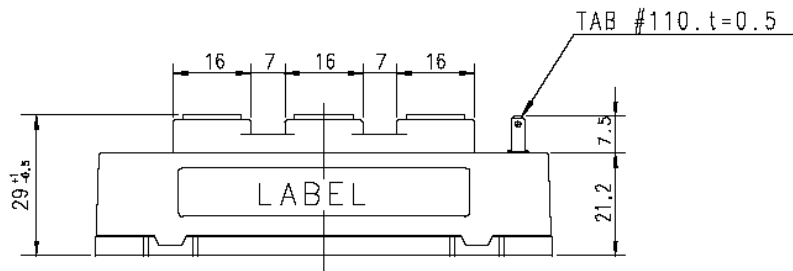
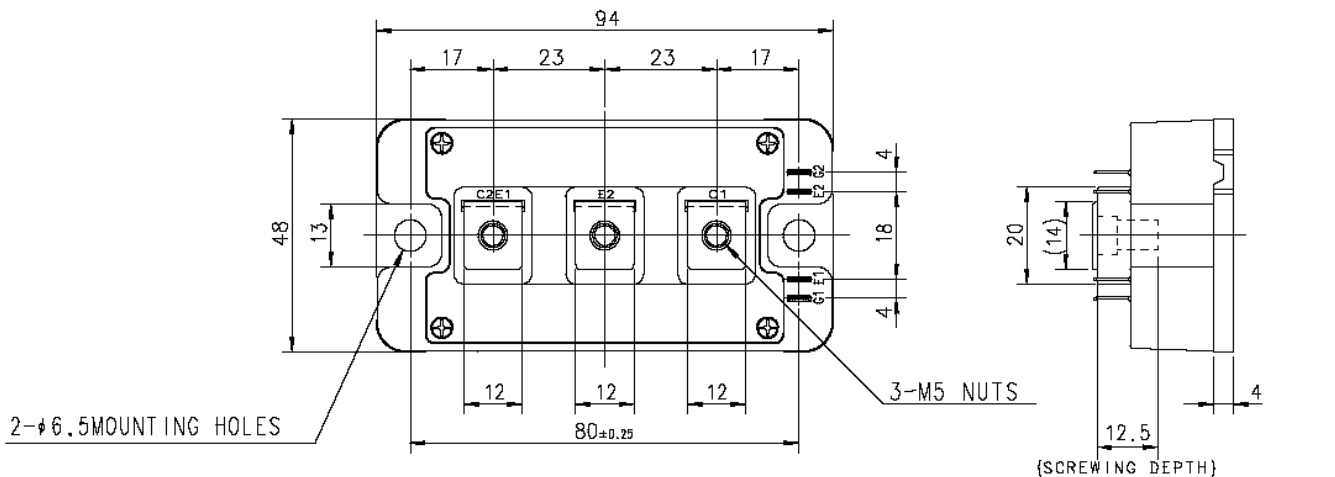
- Flat base Type
- Copper base plate
- RoHS Directive compliant
- UL Recognized under UL1557, File E323585

## APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

## OUTLINE DRAWING & INTERNAL CONNECTION

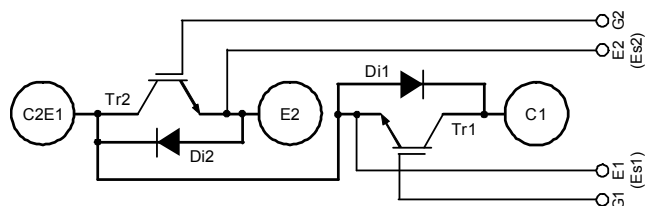
Dimension in mm



Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	$\pm 0.2$
over 3 to 6	$\pm 0.3$
over 6 to 30	$\pm 0.5$
over 30 to 120	$\pm 0.8$
over 120 to 400	$\pm 1.2$

### INTERNAL CONNECTION



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**ABSOLUTE MAXIMUM RATINGS (T<sub>J</sub>=25 °C, unless otherwise specified)**

Symbol	Item	Conditions	Rating	Unit
V <sub>CES</sub>	Collector-emitter voltage	G-E short-circuited	1700	V
V <sub>GES</sub>	Gate-emitter voltage	C-E short-circuited	±20	V
I <sub>C</sub>	Collector current	DC, T <sub>C</sub> =111 °C (Note.2, 4)	75	A
I <sub>CRM</sub>		Pulse, Repetitive (Note.3)	150	
P <sub>tot</sub>	Total power dissipation	T <sub>C</sub> =25 °C (Note.2, 4)	780	W
I <sub>E</sub> (Note.1)	Emitter current	T <sub>C</sub> =25 °C (Note.2, 4)	75	A
I <sub>ERM</sub> (Note.1)		Pulse, Repetitive (Note.3)	150	
T <sub>J</sub>	Junction temperature	-	-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature	-	-40 ~ +125	
V <sub>isol</sub>	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	3500	V

**ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25 °C, unless otherwise specified)**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
I <sub>CES</sub>	Collector-emitter cut-off current	V <sub>CE</sub> =V <sub>CES</sub> , G-E short-circuited	-	-	1.0	mA
I <sub>GES</sub>	Gate-emitter leakage current	V <sub>GE</sub> =V <sub>GES</sub> , C-E short-circuited	-	-	2.0	µA
V <sub>GE(th)</sub>	Gate-emitter threshold voltage	I <sub>C</sub> =7.5 mA, V <sub>CE</sub> =10 V	5.5	7.0	8.5	V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =75 A (Note.5), V <sub>GE</sub> =15 V	-	2.2	2.8	V
		T <sub>J</sub> =25 °C	-	2.45	-	
C <sub>ies</sub>	Input capacitance	V <sub>CE</sub> =10 V, G-E short-circuited	-	-	18.5	nF
C <sub>oes</sub>	Output capacitance		-	-	2.1	
C <sub>res</sub>	Reverse transfer capacitance		-	-	0.4	
Q <sub>G</sub>	Gate charge	V <sub>CC</sub> =1000 V, I <sub>C</sub> =75 A, V <sub>GE</sub> =15 V	-	500	-	nC
t <sub>d(on)</sub>	Turn-on delay time	V <sub>CC</sub> =1000 V, I <sub>C</sub> =75 A, V <sub>GE</sub> =±15 V, R <sub>G</sub> =6.4 Ω, Inductive load	-	-	200	ns
t <sub>r</sub>	Rise time		-	-	150	
t <sub>d(off)</sub>	Turn-off delay time		-	-	550	
t <sub>f</sub>	Fall time		-	-	350	
V <sub>EC</sub> (Note.1)	Emitter-collector voltage	I <sub>E</sub> =75 A (Note.5), G-E short-circuited	-	2.3	3.0	V
t <sub>rr</sub> (Note.1)	Reverse recovery time	V <sub>CC</sub> =1000 V, I <sub>E</sub> =75 A, V <sub>GE</sub> =±15 V, R <sub>G</sub> =6.4 Ω, Inductive load	-	-	300	ns
Q <sub>rr</sub> (Note.1)	Reverse recovery charge	R <sub>G</sub> =6.4 Ω, Inductive load	-	7.5	-	µC
E <sub>on</sub>	Turn-on switching energy per pulse	V <sub>CC</sub> =1000 V, I <sub>C</sub> =I <sub>E</sub> =75 A,	-	15.9	-	mJ
E <sub>off</sub>	Turn-off switching energy per pulse	V <sub>GE</sub> =±15 V, R <sub>G</sub> =6.4 Ω, T <sub>J</sub> =125 °C,	-	22.5	-	
E <sub>rr</sub> (Note.1)	Reverse recovery energy per pulse	Inductive load	-	24.8	-	mJ
r <sub>g</sub>	Internal gate resistance	Per switch, T <sub>c</sub> =25 °C	-	0	-	Ω

**THERMAL RESISTANCE CHARACTERISTICS**

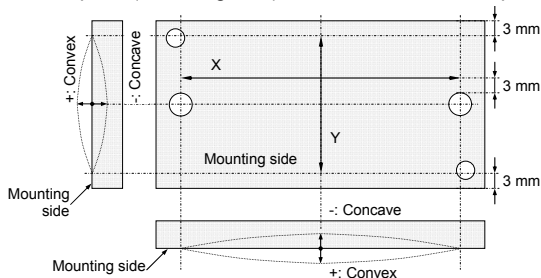
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R <sub>th(j-c)Q</sub>	Thermal resistance (Note.2)	Junction to case, per IGBT	-	-	0.16	K/W
R <sub>th(j-c)D</sub>		Junction to case, per FWDi	-	-	0.29	K/W
R <sub>th(c-s)</sub>	Contact thermal resistance (Note.2)	Case to heat sink, per 1/2 module, Thermal grease applied (Note.6)	-	0.022	-	K/kW

**MECHANICAL CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M <sub>t</sub>	Mounting torque	Main terminals M 5 screw	2.5	3.0	3.5	N·m
M <sub>s</sub>		Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
m	Weight	-	-	310	-	g
e <sub>c</sub>	Flatness of base plate	On the centerline X, Y (Note.7)	-100	-	+100	µm

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- Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).  
 2. Case temperature ( $T_c$ ) and heat sink temperature ( $T_s$ ) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.  
 The heat sink thermal resistance should measure just under the chips.  
 3. Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) dose not exceed  $T_{jmax}$  rating.  
 4. Junction temperature ( $T_j$ ) should not increase beyond  $T_{jmax}$  rating.  
 5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.  
 6. Typical value is measured by using thermally conductive grease of  $\lambda=0.9$  W/(m·K).  
 7. Base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.

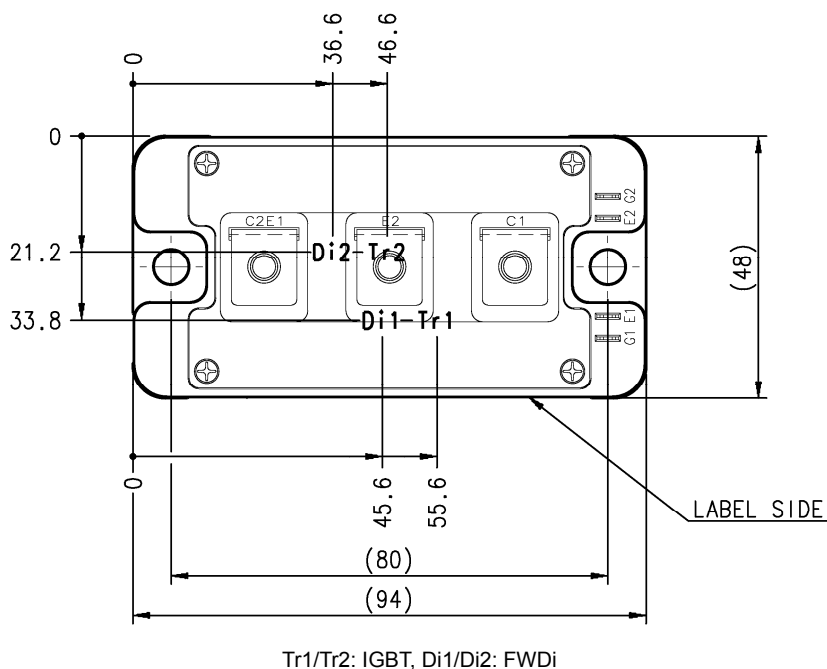


**RECOMMENDED OPERATING CONDITIONS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{CC}$	(DC) Supply voltage	Applied across C1-E2	-	1000	1100	V
$V_{GEon}$	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2	13.5	15.0	16.5	V
$R_G$	External gate resistance	Per switch	6.4	-	64	$\Omega$

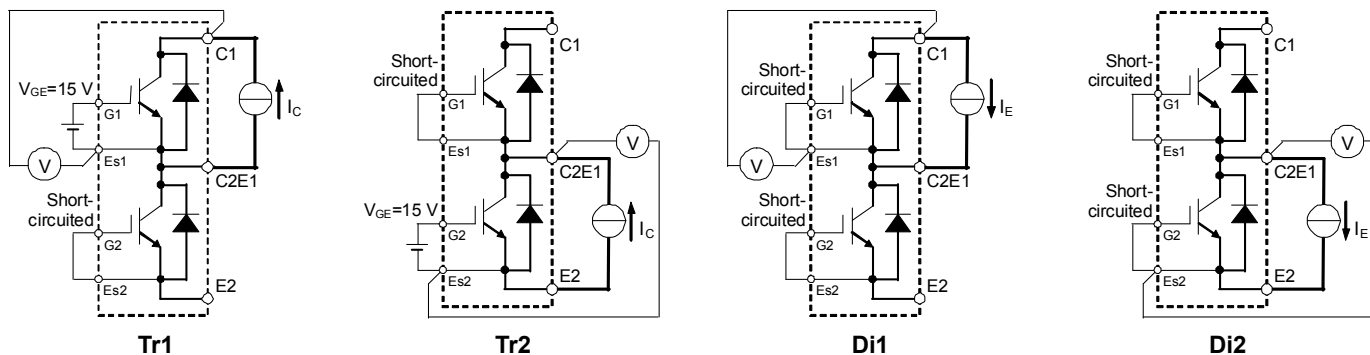
**CHIP LOCATION (Top view)**

Dimension in mm, tolerance:  $\pm 1$  mm



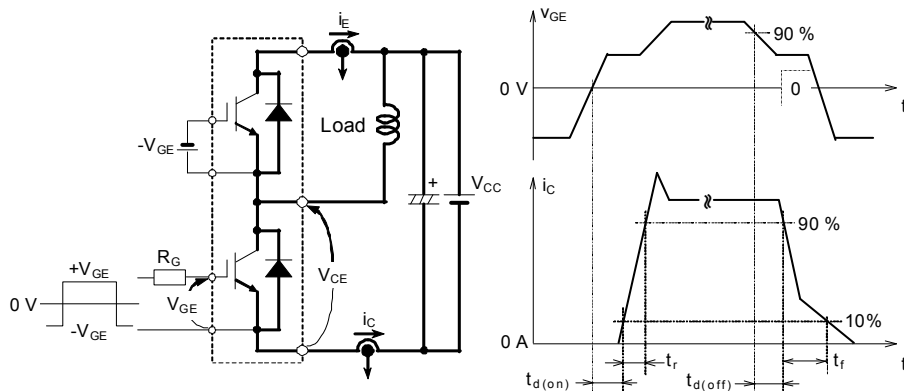
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**TEST CIRCUIT AND WAVEFORMS**

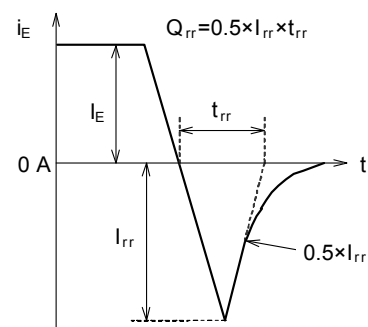


**$V_{CEsat}$  test circuit**

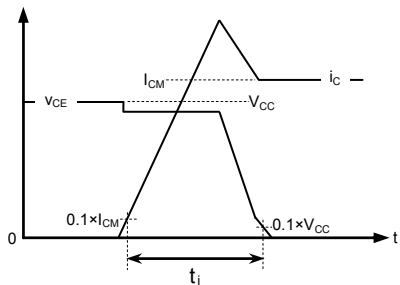
**$V_{EC}$  test circuit**



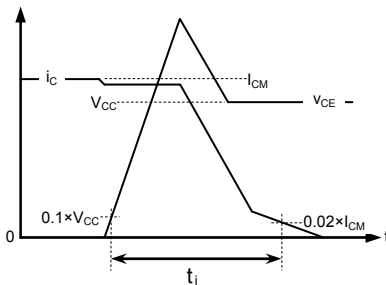
**Switching characteristics test circuit and waveforms**



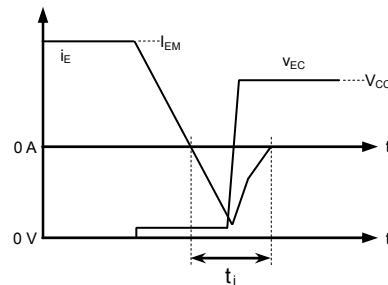
**$t_{rr}$ ,  $Q_{rr}$  test waveform**



**IGBT Turn-on switching energy**



**IGBT Turn-off switching energy**



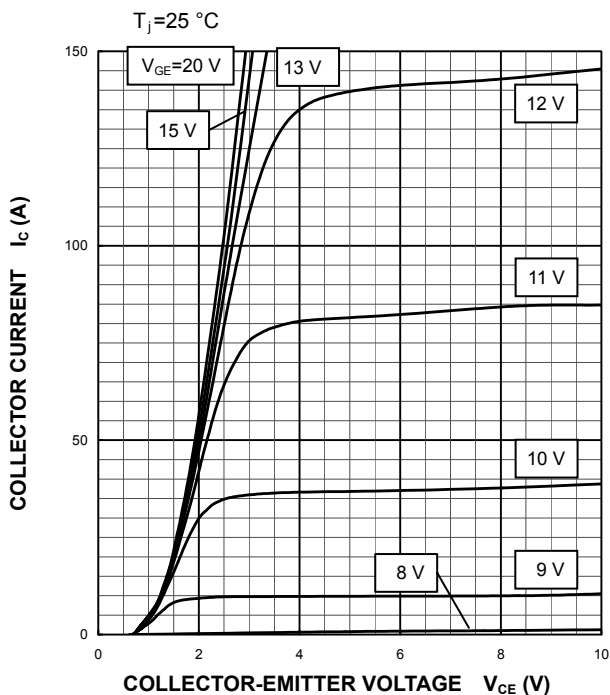
**FWDi Reverse recovery energy**

**Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)**

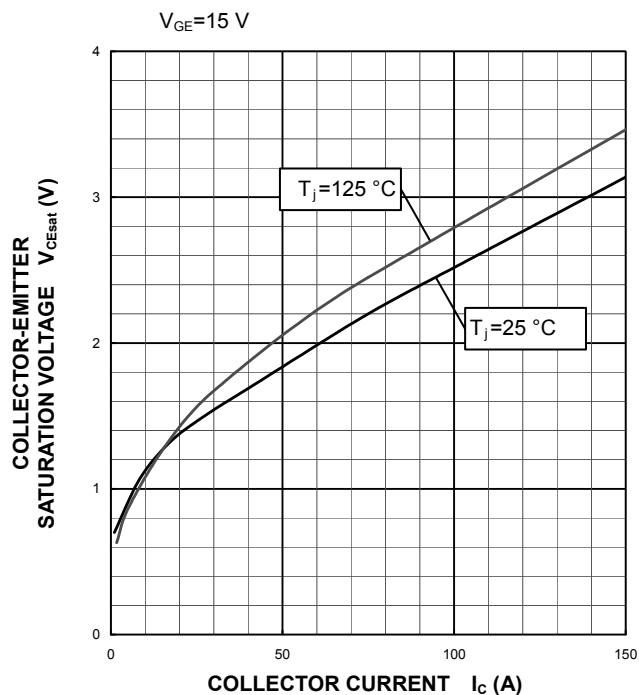
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PERFORMANCE CURVES

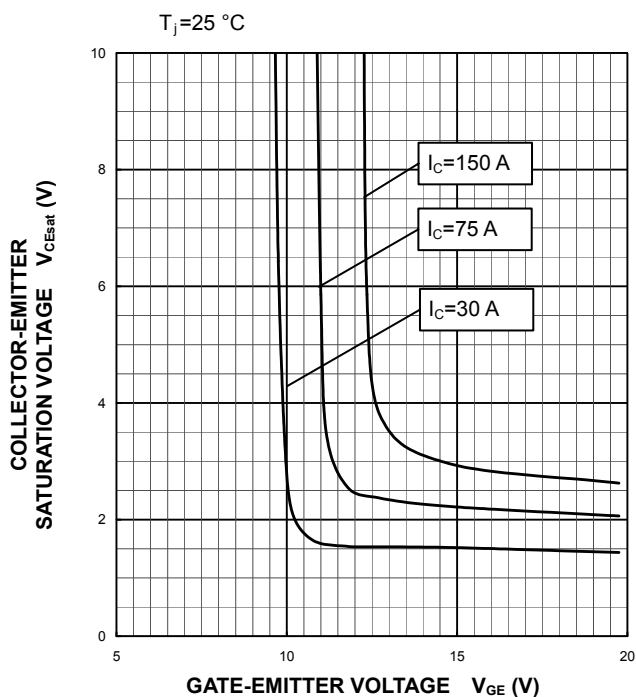
OUTPUT CHARACTERISTICS  
 (TYPICAL)



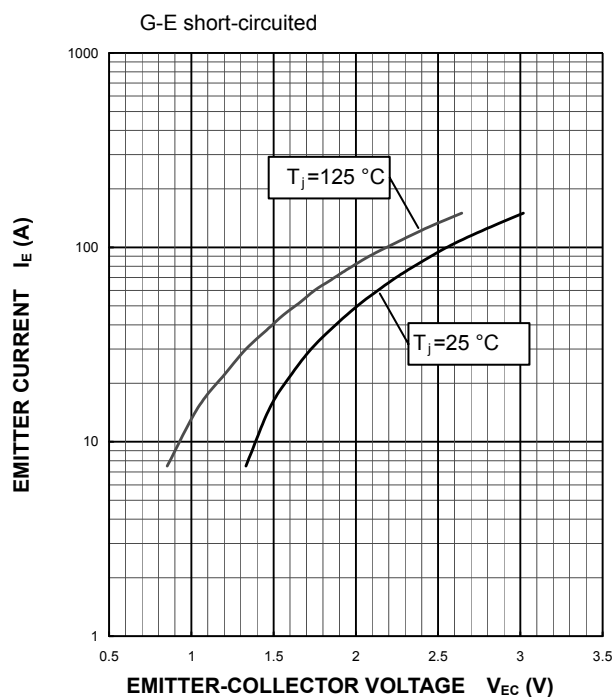
COLLECTOR-EMITTER SATURATION  
 VOLTAGE CHARACTERISTICS  
 (TYPICAL)



COLLECTOR-EMITTER SATURATION  
 VOLTAGE CHARACTERISTICS  
 (TYPICAL)



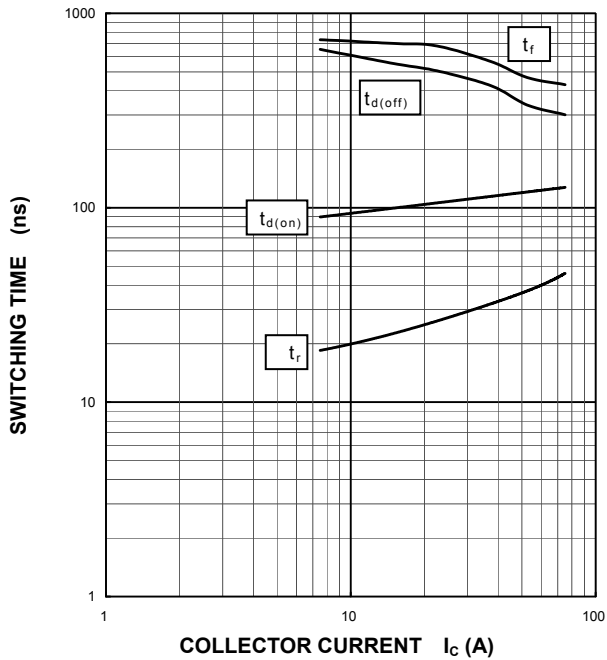
FREE WHEELING DIODE  
 FORWARD CHARACTERISTICS  
 (TYPICAL)



PERFORMANCE CURVES

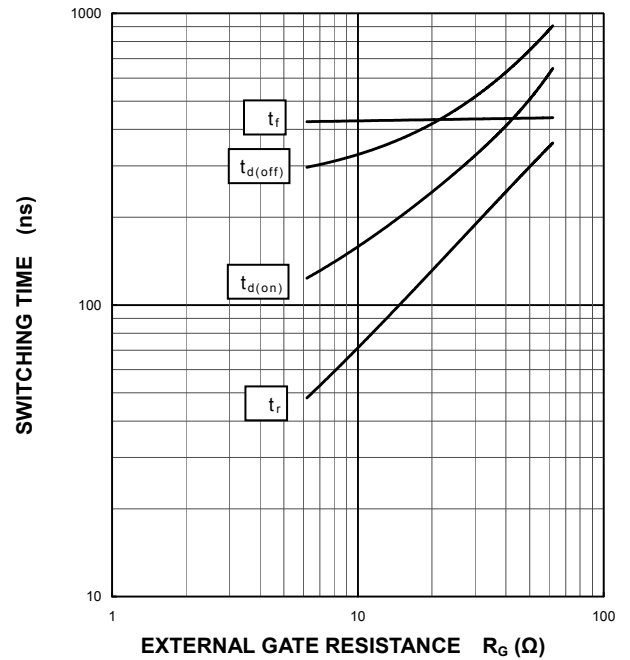
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)

$V_{CC}=1000\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=6.4\ \Omega$ ,  
 $T_J=125\text{ }^\circ\text{C}$ , INDUCTIVE LOAD



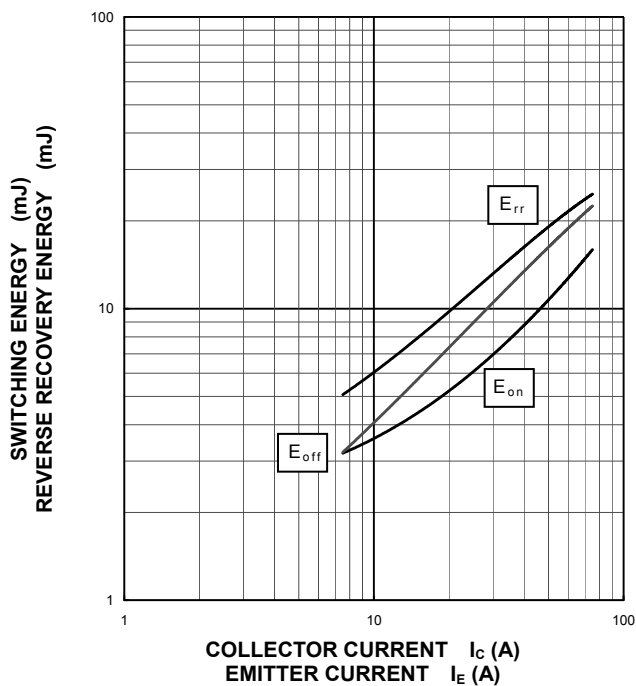
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)

$V_{CC}=1000\text{ V}$ ,  $I_C=75\text{ A}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  
 $T_J=125\text{ }^\circ\text{C}$ , INDUCTIVE LOAD



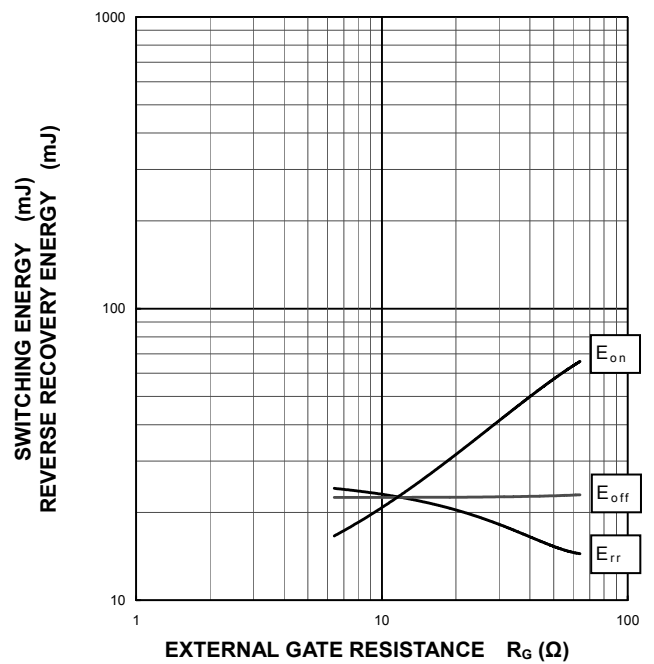
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)

$V_{CC}=1000\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=6.4\ \Omega$ ,  $T_J=125\text{ }^\circ\text{C}$   
INDUCTIVE LOAD, PER PULSE



HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)

$V_{CC}=1000\text{ V}$ ,  $I_C/I_E=75\text{ A}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $T_J=125\text{ }^\circ\text{C}$   
INDUCTIVE LOAD, PER PULSE

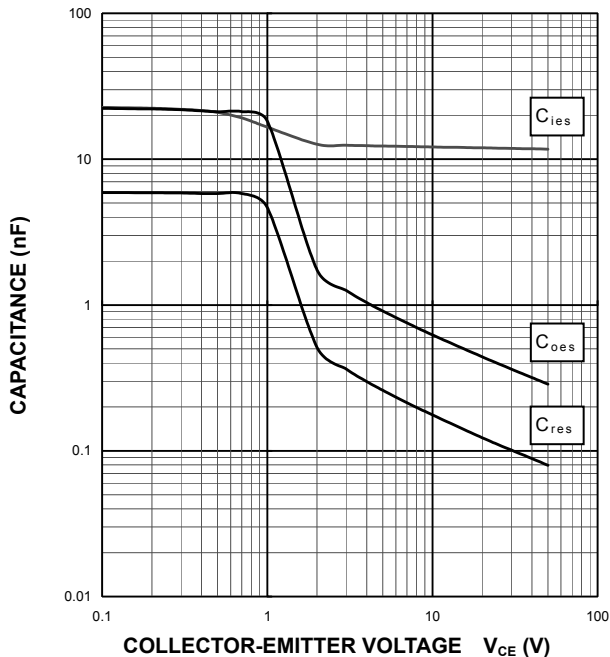


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PERFORMANCE CURVES

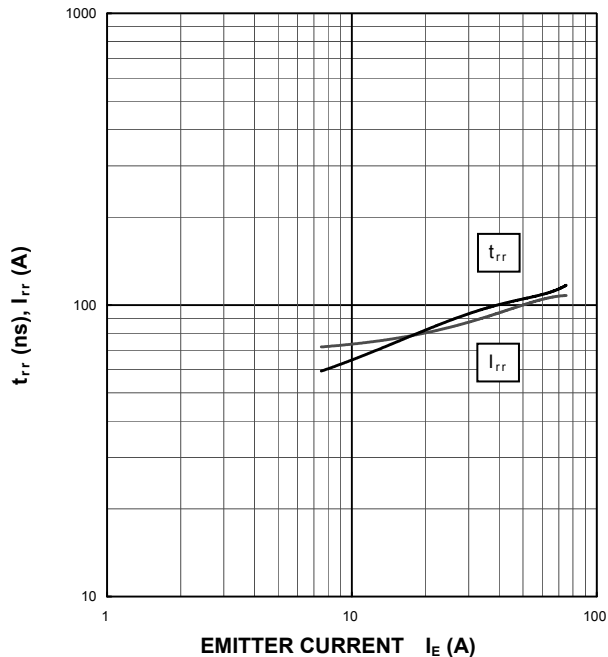
**CAPACITANCE CHARACTERISTICS  
 (TYPICAL)**

G-E short-circuited,  $T_j=25\text{ }^\circ\text{C}$



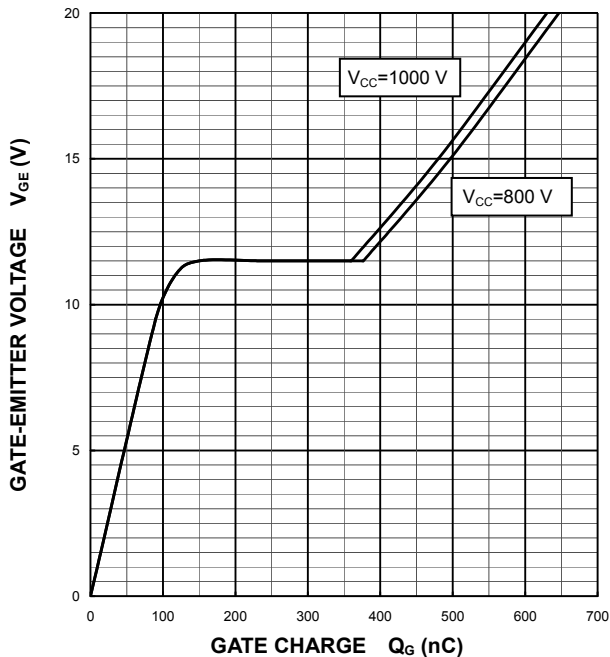
**FREE WHEELING DIODE  
 REVERSE RECOVERY CHARACTERISTICS  
 (TYPICAL)**

$V_{CC}=1000\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=6.4\ \Omega$ ,  
 $T_j=25\text{ }^\circ\text{C}$ , INDUCTIVE LOAD



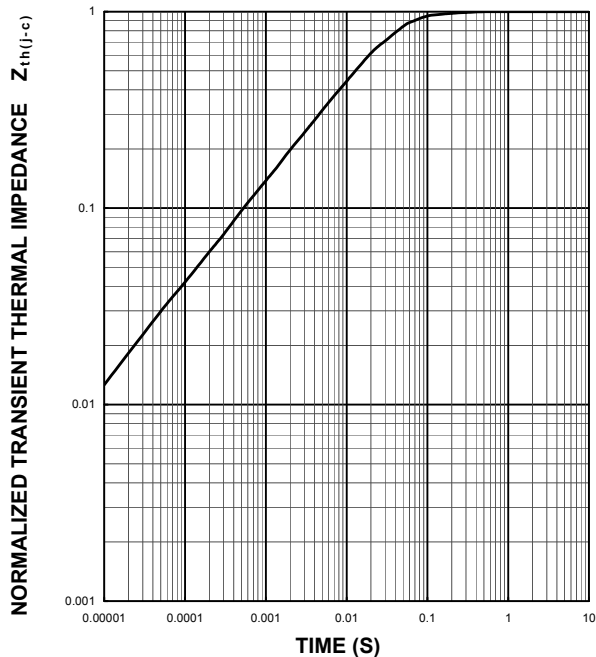
**GATE CHARGE CHARACTERISTICS  
 (TYPICAL)**

$I_C=75\text{ A}$ ,  $T_j=25\text{ }^\circ\text{C}$



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS  
 (MAXIMUM)**

Single pulse,  $T_C=25\text{ }^\circ\text{C}$   
 $R_{th(j-c)Q}=0.16\text{ K/W}$ ,  $R_{th(j-c)D}=0.29\text{ K/W}$



### **Keep safety first in your circuit designs!**

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